

**2SC5662 / 2SC4726H / 2SC4726 / 2SC4083 /
2SC3838K / 2SC4043S**

- 1) High transition frequency. (Typ. $f_T = 1.5\text{GHz}$)
- 2) Small $r_{bb'}$, C_c and high gain. (Typ. 4ps)
- 3) Small N_F .

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CB0}	20	V
Collector-emitter voltage		V _{CE0}	11	V
Emitter-base voltage		V _{EB0}	3	V
Collector current		I _c	50	mA
Collector power dissipation	2SC5662, 2SC4726H, 2SC4726	P _c	0.15	W
	2SC4083, 2SC3838K		0.2	
	2SC4043S		0.3	
Junction temperature		T _j	150	°C
Storage temperature		T _{stg}	-55~+150	°C

Type	2SC5662	2SC4726H	2SC4726	2SC4083	2SC3838K	2SC4043S
Package	VMT3	EMT3H	EMT3	UMT3	SMT3	SPT
Pin	NP	NP	NP	NP	NP	NP
Marking	AD	AD	AD	1D	AD	—
Code	T2L	T2L	TL	T106	T146	TP
Basic ordering unit (pieces)	8000	8000	3000	3000	3000	5000

2SC5662		(1) Base (2) Emitter (3) Collector
ROHM : VMT3		
2SC4726H		(1) Base (2) Emitter (3) Collector
ROHM : EMT3 Flat lead EIAJ : SC-89		
Each lead has same dimensions		
2SC4726		(1) Emitter (2) Base (3) Collector
ROHM : EMT3 EIAJ : SC-75A		
2SC4083		(1) Emitter (2) Base (3) Collector
ROHM : UMT3 EIAJ : SC-70		
Each lead has same dimensions		
2SC3838K		(1) Emitter (2) Base (3) Collector
ROHM : SMT3 EIAJ : SC-59		
Each lead has same dimensions		
2SC4043S		(1) Emitter (2) Collector (3) Base
ROHM : SPT EIAJ : SC-72		
Taping specifications		

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Transistors

●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage		BV _{CB0}	20	—	—	V	I _C = 10μA
Collector-emitter breakdown voltage		BV _{CEO}	11	—	—	V	I _C = 1mA
Emitter-base breakdown voltage		BV _{EB0}	3	—	—	V	I _E = 10μA
Collector cutoff current		I _{CB0}	—	—	0.5	μA	V _{CB} = 10V
Emitter cutoff current		I _{EB0}	—	—	0.5	μA	V _{EB} = 2V
Collector-emitter saturation voltage		V _{CE(sat)}	—	—	0.5	V	I _C /I _B = 10mA/5mA
DC current transfer ratio	2SC5662, 2SC4726H, 2SC4726, 2SC4083, 2SC3838K	h _{FE}	56	—	180	—	V _{CE} /I _C = 10V/5mA
	2SC4043S		82	—	180		
Transition frequency		f _T	1.4	3.2	—	GHz	V _{CE} = 10V, I _E = 10mA, f = 500MHz
Output capacitance		C _{ob}	—	0.8	1.5	pF	V _{CB} = 10V, I _E = 0A, f = 1MHz
Collector-base time constant		τ _{bt} ·C _C	—	4	12	ps	V _{CB} = 10V, I _C = 10mA, f = 31.8MHz
Noise factor		NF	—	3.5	—	dB	V _{CE} = 6V, I _C = 2mA, f = 500MHz, R _g = 50Ω